

**What is Claimed is:**

1. A method for fabricating a semiconductor device, comprising the steps of:

5 sequentially forming a gate insulating film and a conductive layer for gate electrode on a semiconductor substrate;

forming a multi-layered hard mask layer on the conductive layer, wherein each layer of the multi-layered  
10 hard mask layer is formed of materials different from one another;

etching the hard mask layer, the conductive layer and the gate insulting film using a gate electrode mask to form a stacked structure of a gate insulating film pattern, a  
15 gate electrode and a hard mask layer pattern;

forming an insulating film spacer on a sidewall of the stacked structure;

forming an interlayer insulating film on the entire surface;

20 etching the interlayer insulating film using a landing plug contact etching mask to form a landing plug contact hole exposing the semiconductor substrate;

forming a conductive layer for a landing plug on the entire surface to fill the landing plug contact hole; and

planarizing the conductive layer for a landing plug  
to form a landing plug.

2. The method according to claim 1, wherein the  
5 hard mask layer comprises a stacked structure of nitride  
film/oxide film/nitride film.